Supporting Information

Enhanced Light-Emitting Transistors Utilizing Multi-Dimensional $CsPbBr_3$ Perovskite Films and PVP-Modified ZTO Semiconductor Layers

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Key Words: Multi-dimensional perovskite film; Light emitting transistor; $CsPbBr_3$; PVP modification; Metal oxide semiconductor

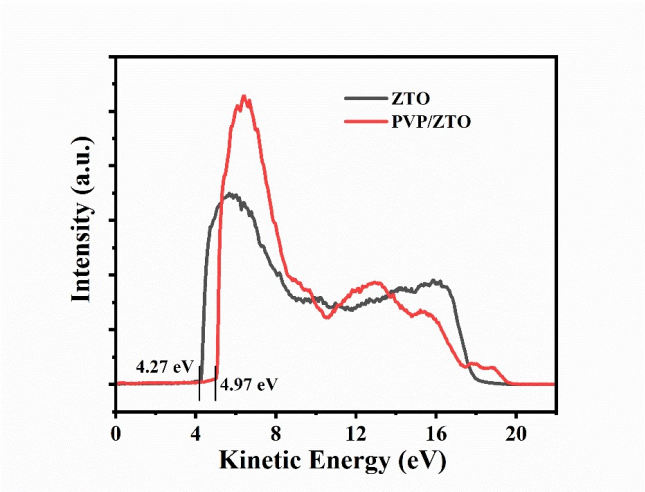

Figure S1 UPS spectrum of ZTO surface before and after PVP modification.

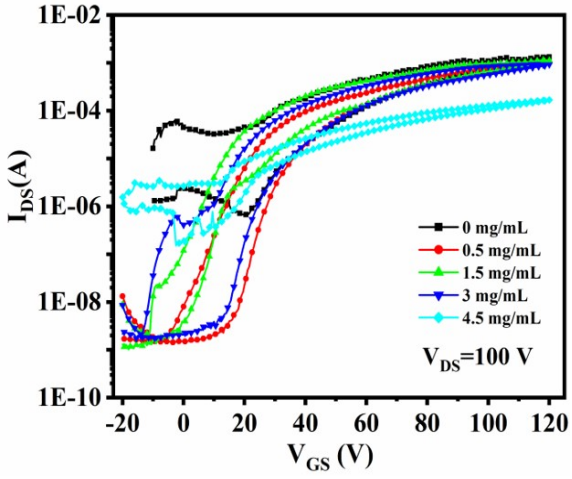

Figure S2 Transfer curves of devices under different PVP concentrations.

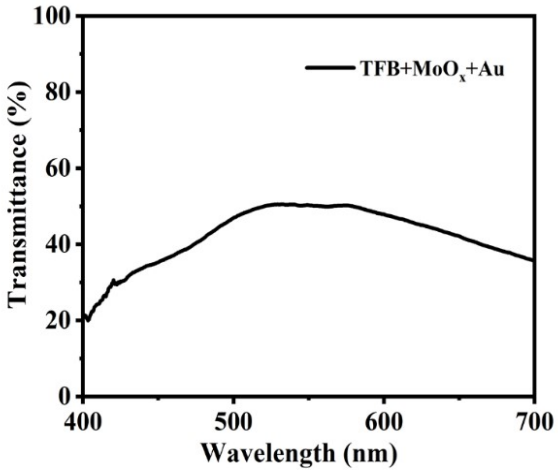

Figure S3 Transmission spectra of TFB, MoO_x and Au.

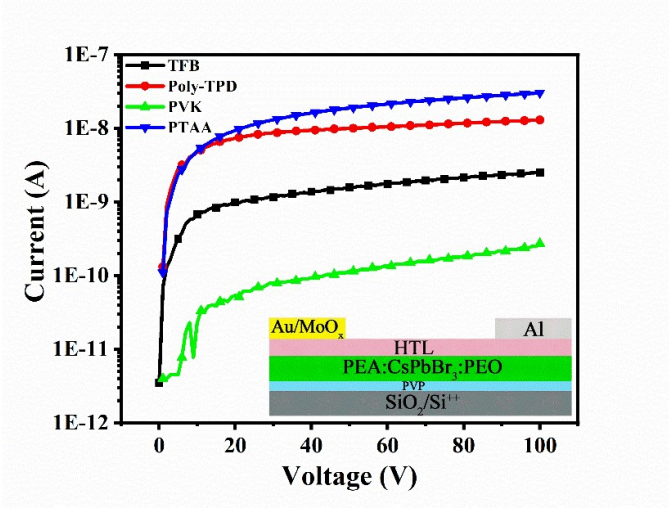

Figure S4 Diode current curve of the device without channel layer.

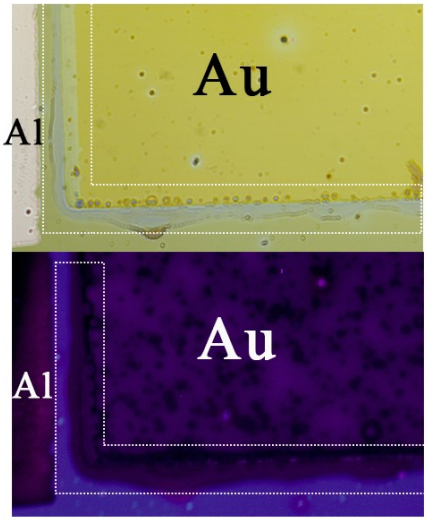

Figure S5 Electrode edge doping after operation of Poly-TPD light-emitting transistor.

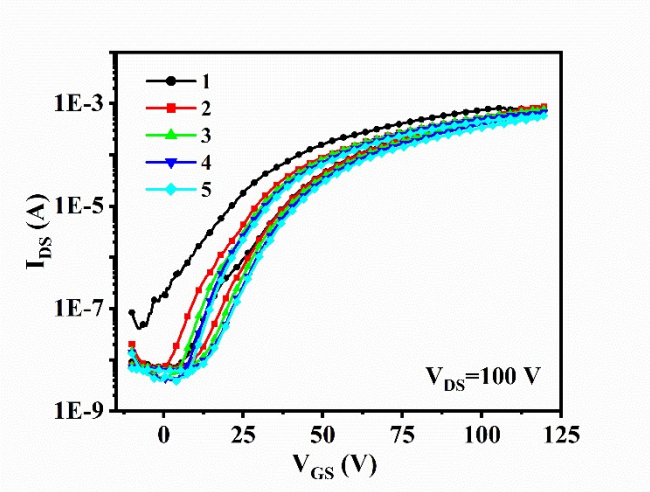

Figure S6 Cyclic scan transfer curve of the device.

Figure S7 Transfer curve and photocurrent curve of the device under different TFB concentrations.